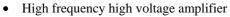


2SC3380 Silicon NPN Triple Diffused

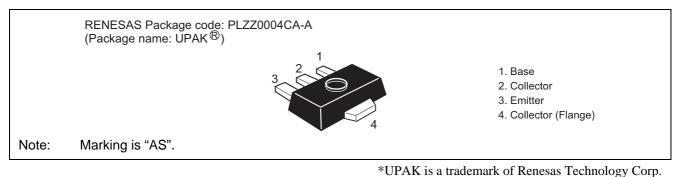
REJ03G0713-0300 (Previous ADE-208-1082A) Rev.3.00 Aug.10.2005

Application



• High voltage switch

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	300	V
Collector to emitter voltage	V _{CEO}	300	V
Emitter to base voltage	V _{EBO}	5	V
Collector current	Ι _C	100	mA
Collector power dissipation	Pc*1	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)



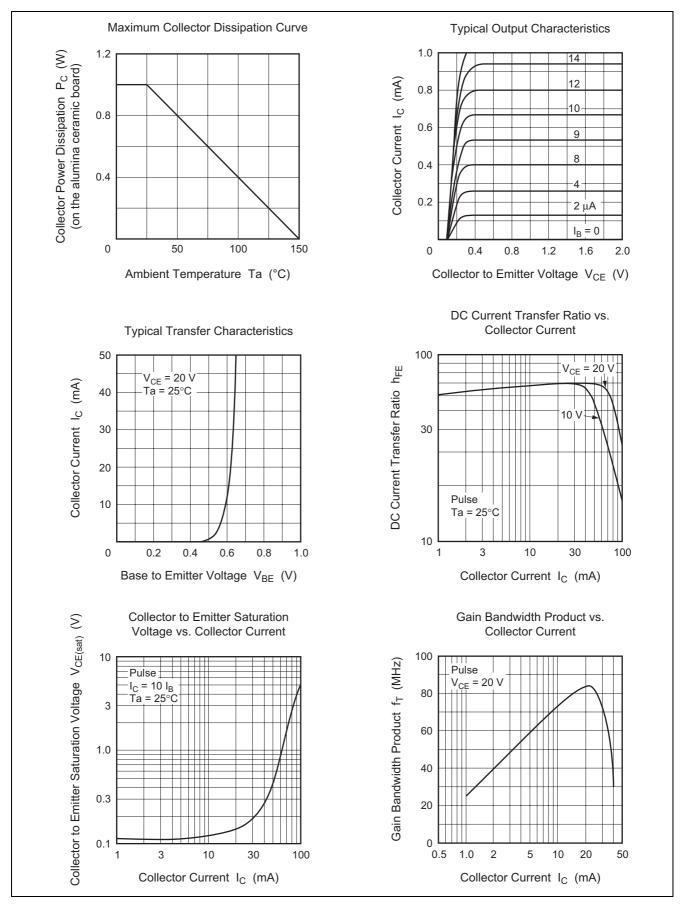
Electrical Characteristics

(1a - 25C)

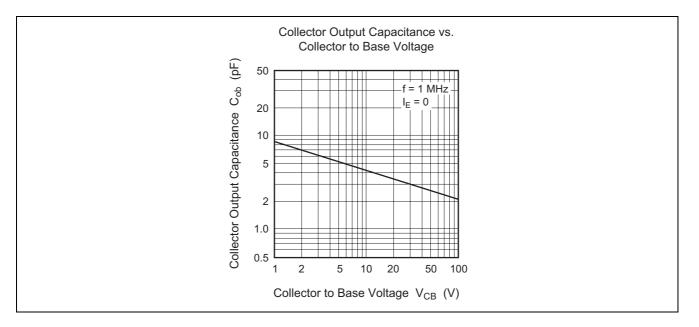
ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	300	—		V	$I_{C} = 10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	V _{(BR)CEO}	300	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	V _{(BR)EBO}	5	_	_	V	$I_E = 10 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CEO}	_	—	1	μA	V_{CE} = 250 V, R_{BE} = ∞
Collector to emitter saturation voltage	V _{CE(sat)}	_	—	1.5	V	$I_{C} = 20 \text{ mA}, I_{B} = 2 \text{ mA}$
DC current transfer ratio	h _{FE}	30	—	200		$V_{CE} = 20 \text{ V}, I_{C} = 20 \text{ mA}$
Gain bandwidth product	f⊤		80		MHz	$V_{CE} = 20 \text{ V}, I_C = 20 \text{ mA}$
Collector output capacitance	Cob		_	4	pF	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$



Main Characteristics

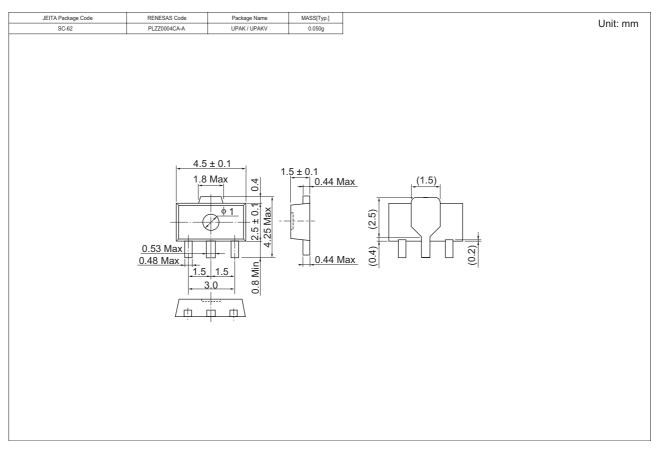








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SC3380ASTR-E	1000	φ 178 mm Reel, 12 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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